Abstracts

Sub-Half-Micron GaAs FETs for Applications Through K Band

C. Huang, A. Herbig and R. Anderson. "Sub-Half-Micron GaAs FETs for Applications Through K Band." 1981 MTT-S International Microwave Symposium Digest 81.1 (1981 [MWSYM]): 25-27.

Sub-half-micron gate GaAs FETs fabricated on high quality VPE buffer material have achieved state-of-the-art low noise performances. Best noise figures of 0.58 dB at 4 GHz and 1.29 dB at 12 GHz have been observed. Power added efficiency of 35% at Ku band is also reported.

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